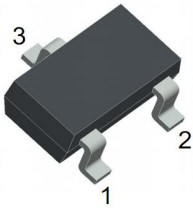
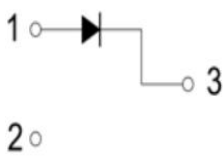
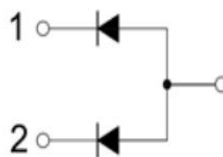
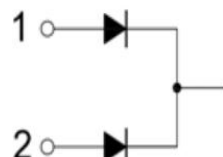
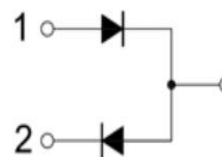


Switching Diodes	SOT-23 Plastic-Encapsulate Diodes
<p style="text-align: center;"><u>SOT-23</u></p> 	<p>Features</p> <ul style="list-style-type: none"> • High Conductance • Fast Switching Speed • For General Purpose Switching Applications

MMBD4148A	MMBD4148CA	MMBD4148CC	MMBD4148SE
			
MARKING:5H	MARKING:D6	MARKING:D5	MARKING:D4

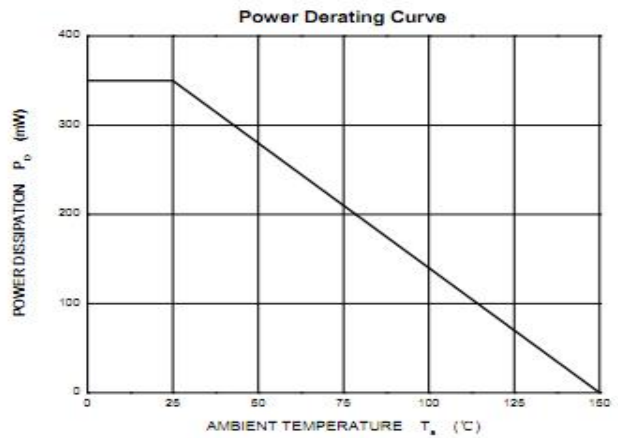
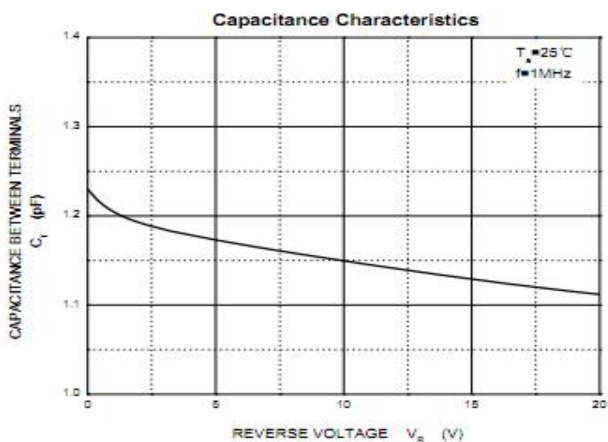
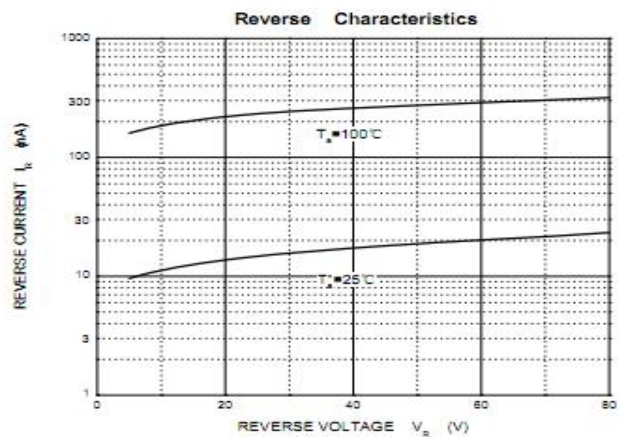
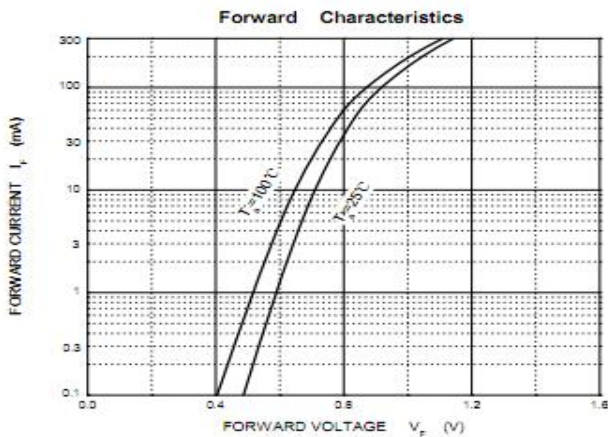
Solid dot = Green molding compound device, if none, the normal device.

Maximum ratings (@Ta=25°C)

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	VRM	100	V
Peak Repetitive Peak Reverse Voltage	VRRM	100	V
Working Peak Reverse Voltage	VRWM	100	V
DC Blocking Voltage	VR	100	V
RMS Reverse Voltage	VR(RMS)	72	V
Forward Continuous Current	IFM	300	mA
Average Rectified Output Current	Io	200	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	IFSM	2.0	A
Power Dissipation	PD	350	mW
Thermal Resistance from Junction to Ambient	RθJA	357	°C/W
Junction Temperature	TJ	150	°C
Storage Temperature Range	TSTG	-55~+150	°C

Electrical ratings (@Ta=25°C)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse breakdown voltage	V(BR)1	IR=100µA	100			V
	V(BR)2	IR=100µA	75			V
Forward voltage	VF2	IF=10mA			1	V
Reverse current	IR1	VR=75V			5	uA
	IR2	VR=25V			25	nA
Capacitance between terminals	Ctot	VR=0V, f=1MHz			4	PF
Reverse recovery time	t _{rr}	IF=IR=10mA, VR=6V Irr=0.1×IR, RL= 100 Ω			4	nS

Typical Characteristics



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)